

Product Summary

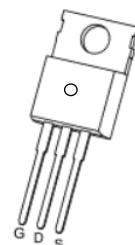
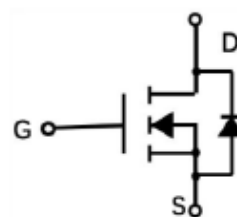
$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
100V	4.3mΩ@10V	128A

Feature

- Split Gate Trench Technology
- Low $R_{DS(on)}$
- Low Gate Charge
- Low Gate Resistance
- 100% UIS Tested

Application

- Power Switching Application

TO-220-3L-C

Schematic diagram

Package Marking and Ordering Information

Part Number	Package	Marking	Packing	Reel Size	Tape Width	Qty
GPT042N10NTB	TO-220-3L-C	T042N10N	Tube	NA	NA	50pcs

ABSOLUTE MAXIMUM RATINGS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain - Source Voltage		V_{DS}	100	V
Gate - Source Voltage		V_{GS}	±20	V
Continuous Drain Current ¹	$T_C = 25^\circ\text{C}$	I_D	128	A
	$T_C = 100^\circ\text{C}$	I_D	81	A
Pulsed Drain Current ²		I_{DM}	512	A
Single Pulsed Avalanche Current ³		I_{AS}	81	A
Single Pulsed Avalanche Energy ³		E_{AS}	328	mJ
Power Dissipation ⁵		P_D	178	W
$T_C = 25^\circ\text{C}$				
Thermal Resistance from Junction to Ambient ⁶		$R_{\theta JA}$	46	$^\circ\text{C/W}$
Thermal Resistance from Junction to Case		$R_{\theta JC}$	0.7	$^\circ\text{C/W}$
Junction Temperature		T_J	150	$^\circ\text{C}$
Storage Temperature		T_{STG}	-55~ +150	$^\circ\text{C}$

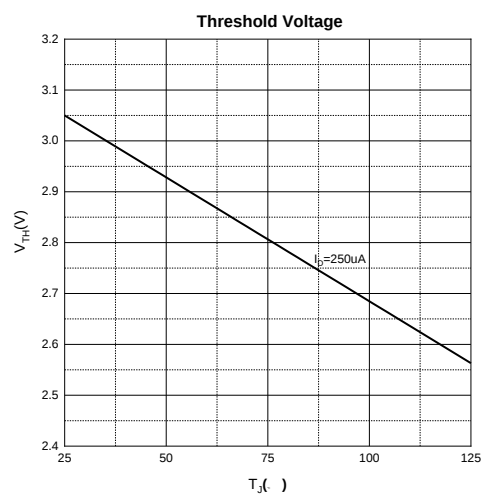
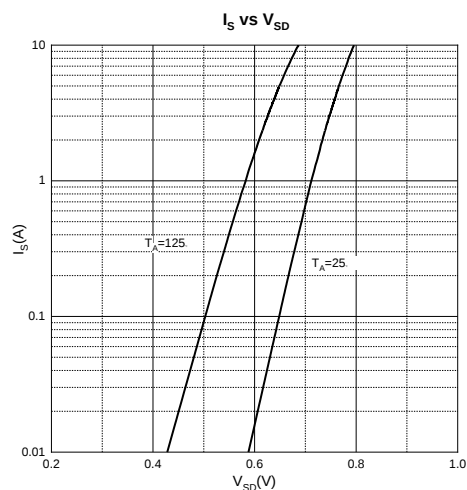
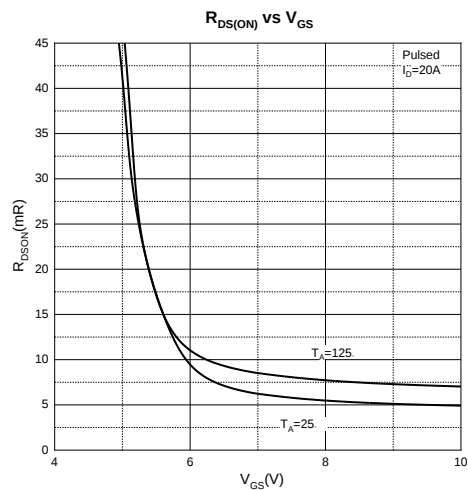
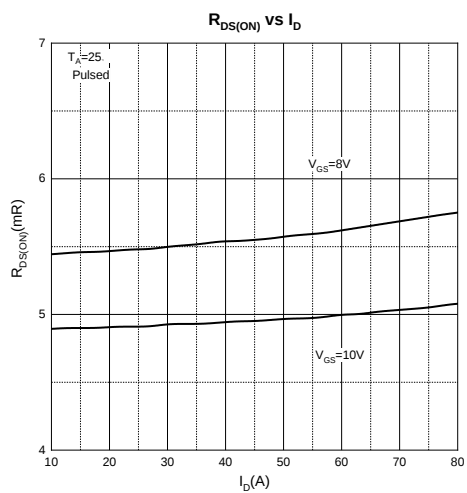
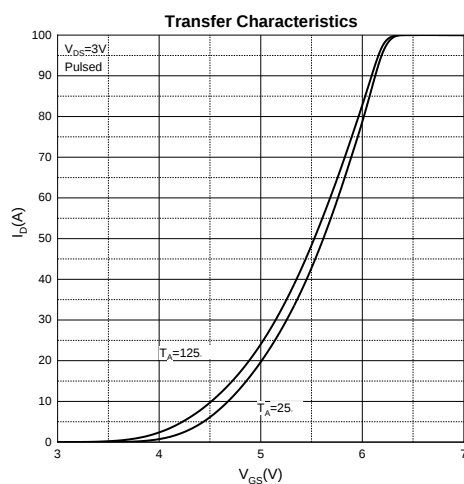
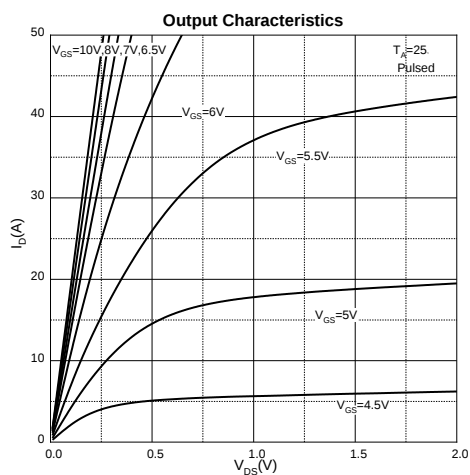
MOSFET ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted)

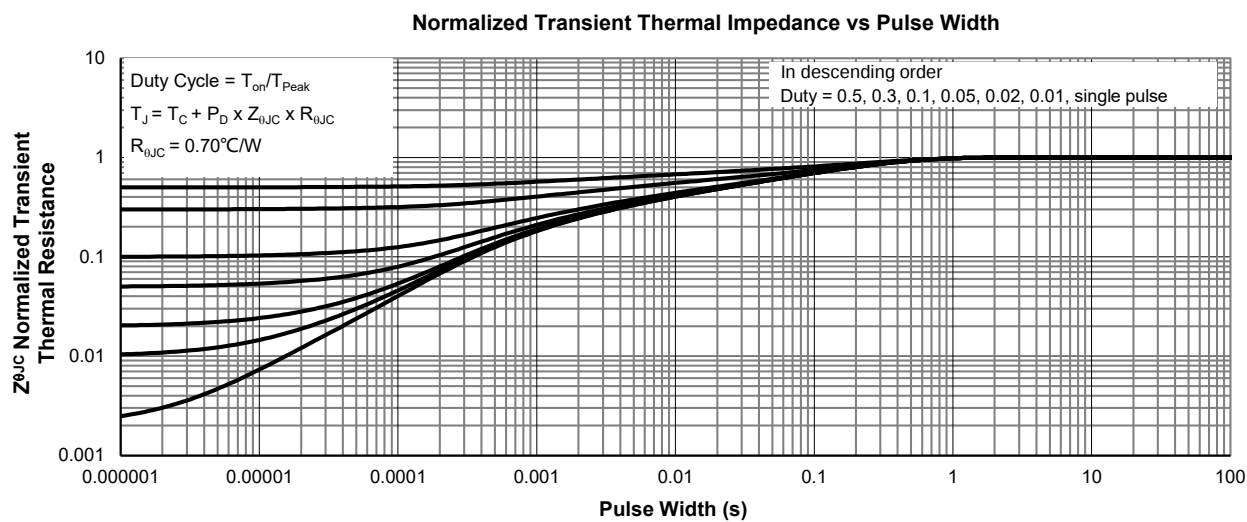
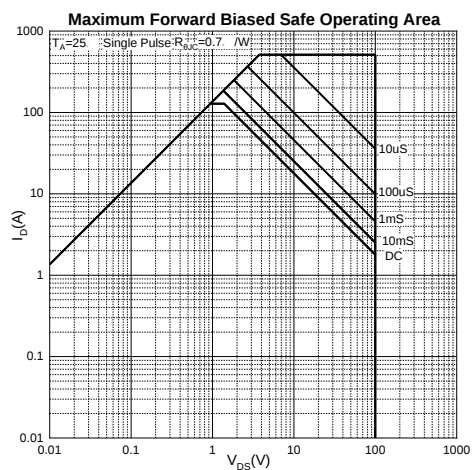
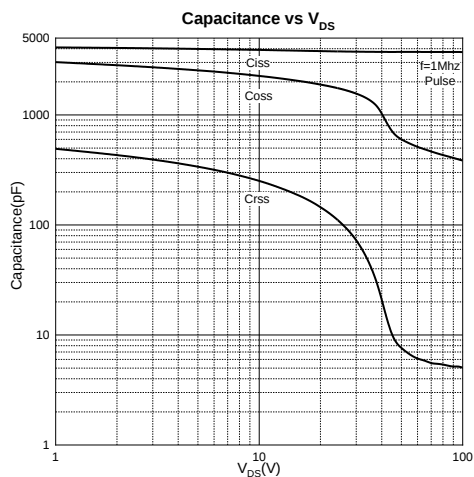
Parameter	Symbol	Test Condition	Min	Type	Max	Unit
Off Characteristics						
Drain - Source Breakdown Voltage	$V_{(BR)DSS}$	$V_{GS} = 0V, I_D = 250\mu A$	100			V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = 100V, V_{GS} = 0V$			1	μA
Gate - Body Leakage Current	I_{GSS}	$V_{GS} = \pm 20V, V_{DS} = 0V$			± 100	nA
On Characteristics ⁴						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}, I_D = 250\mu A$	2	3	4	V
Drain-source On-resistance	$R_{DS(on)}$	$V_{GS} = 10V, I_D = 10A$		4.3	5.4	m Ω
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS} = 50V, V_{GS} = 0V, f = 1MHz$		3765		pF
Output Capacitance	C_{oss}			592		
Reverse Transfer Capacitance	C_{rss}			6.2		
Gate Resistance	R_g	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$		2.4		Ω
Switching Characteristics						
Total Gate Charge	Q_g	$V_{DS} = 50V, V_{GS} = 10V, I_D = 20A$		60		nC
Gate-source Charge	Q_{gs}			4.9		
Gate-drain Charge	Q_{gd}			18.9		
Turn-on Delay Time	$t_{d(on)}$	$V_{DD} = 50V, V_{GS} = 10V, R_G = 3\Omega, R_L = 2.5\Omega$		18		ns
Turn-on Rise Time	t_r			23		
Turn-off Delay Time	$t_{d(off)}$			37		
Turn-off Fall Time	t_f			15.7		
Source - Drain Diode Characteristics						
Diode Forward Voltage ⁴	V_{SD}	$V_{GS} = 0V, I_S = 1A$			1.0	V

Notes :

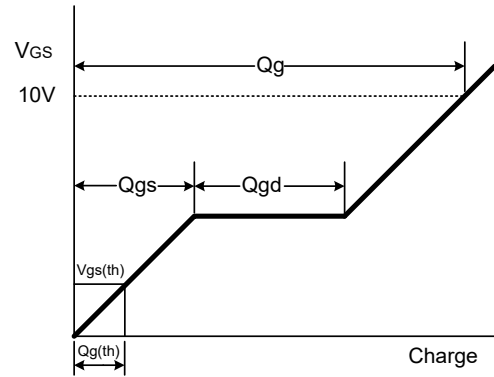
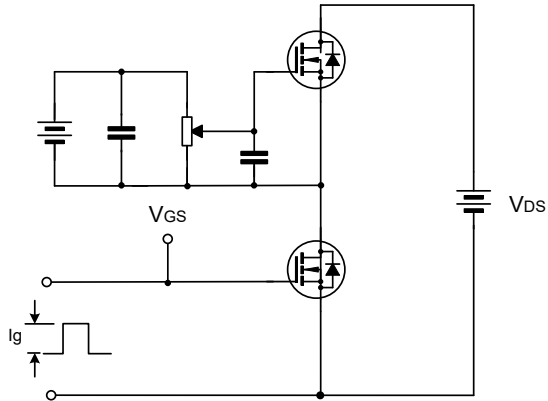
- 1.The maximum current rating is limited by package.And device mounted on a large heatsink
- 2.Pulse Test : Pulse Width $\leq 10\mu s$, duty cycle $\leq 1\%$.
- 3.EAS condition: $V_{DD} = 50V, V_{GS} = 10V, L = 3mH, R_G = 25\Omega$ Starting $T_J = 25^\circ\text{C}$.
- 4.Pulse Test : Pulse Width $\leq 300\mu s$, duty cycle $\leq 2\%$.
- 5.The power dissipation P_D is limited by $T_{J(MAX)} = 150^\circ\text{C}$.And device mounted on a large heatsink
- 6.Device mounted on $1in^2$ FR-4 board with 2oz. Copper, in a still air environment with $T_A = 25^\circ\text{C}$.

Typical Characteristics

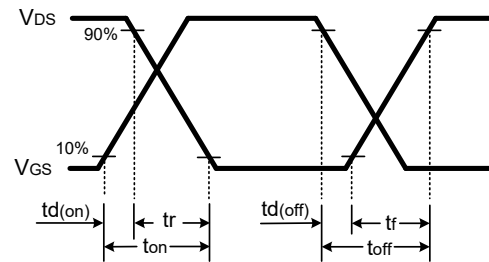
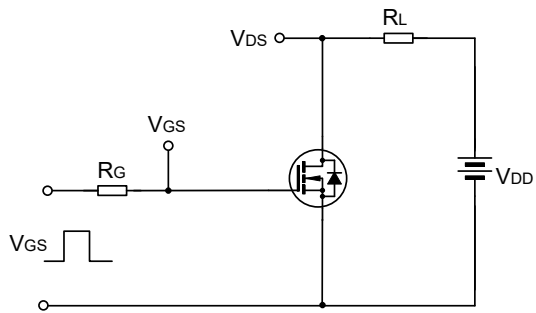




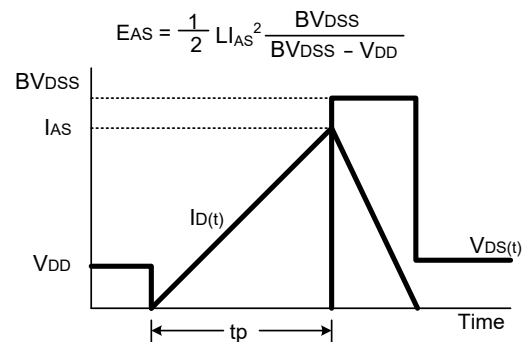
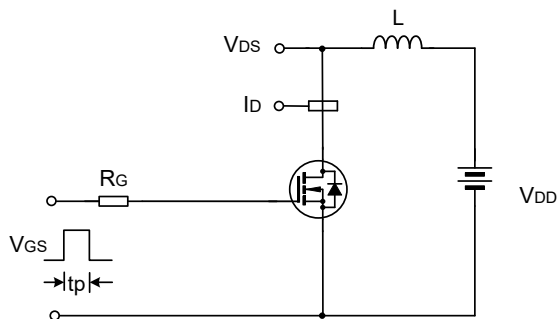
Gate Charge Test Circuit & Waveform

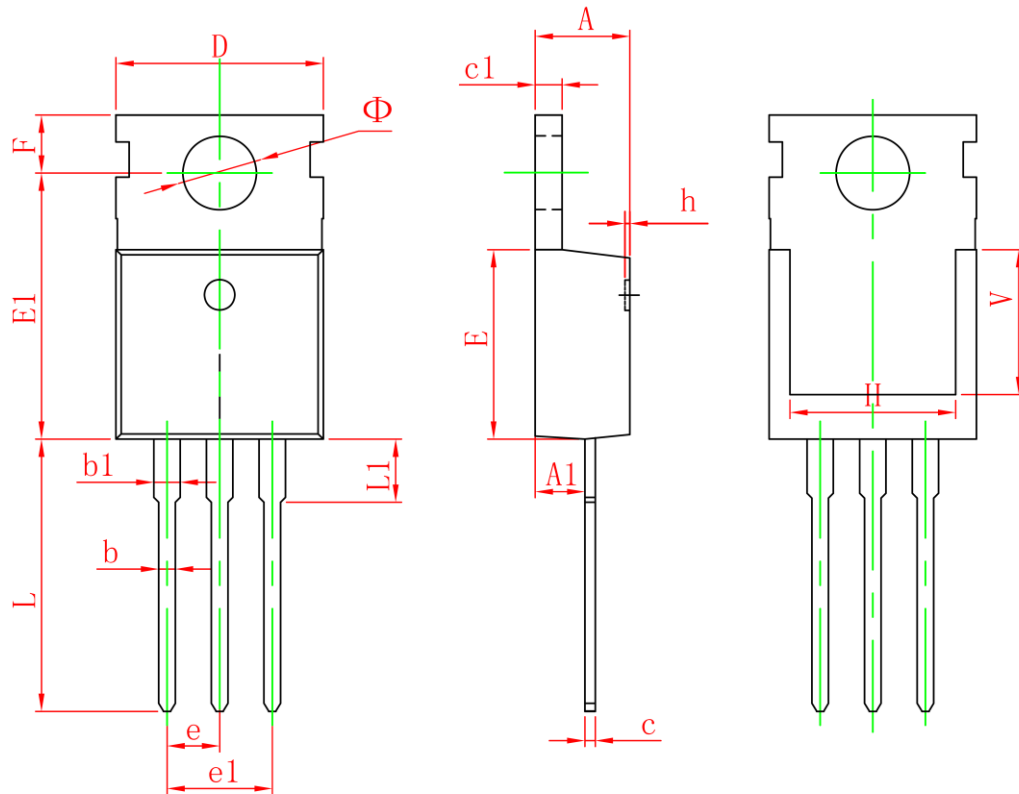


Resistive Switching Test Circuit & Waveform



E_{AS} Test Circuit & Waveform



TO-220-3L-C Package Information


Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	4.400	4.600	0.173	0.181
A1	2.250	2.550	0.089	0.100
b	0.710	0.910	0.028	0.036
b1	1.170	1.370	0.046	0.054
c	0.330	0.650	0.013	0.026
c1	1.200	1.400	0.047	0.055
D	9.910	10.250	0.390	0.404
E	8.950	9.750	0.352	0.384
E1	12.650	13.050	0.498	0.514
e	2.540TYP		0.100TYP	
e1	4.980	5.180	0.196	0.204
F	2.650	2.950	0.104	0.116
H	7.900	8.100	0.311	0.319
h	0.000	0.300	0.000	0.012
L	12.900	13.400	0.508	0.528
L1	2.850	3.250	0.112	0.128
V	6.900REF		0.272REF	
Φ	3.400	3.800	0.134	0.150

Attention:

- GreenPower Electronics reserves the right to improve product design function and reliability without notice.
- Any and all semiconductor products have certain probability to fail or malfunction, which may result in personal injury, death or property damage. Customer are solely responsible for providing adequate safe measures when design their systems.
- GreenPower Electronics products belong to consumer electronics or other civilian electronic products.